

SCIENTIFIC REPORTS

OPEN

Author Correction: Modulation of van der Waals and classical epitaxy induced by strain at the Si step edges in GeSbTe alloys

Eugenio Zallo¹, Stefano Cecchi¹, Jos E. Boschker¹, Antonio M. Mio², Fabrizio Arciprete^{1,3}, Stefania Privitera² & Raffaella Calarco¹

Correction to: *Scientific Reports* <https://doi.org/10.1038/s41598-017-01502-z>, published online 03 May 2017

This Article contains errors in Figure 4b. The colours of the curves in the left panel were inadvertently switched. The correct Figure 4b appears below as Figure 1.

¹Paul-Drude-Institut für Festkörperelektronik, Hausvogteiplatz 5-7, D-10117, Berlin, Germany. ²Institute for Microelectronics and Microsystems (IMM), Consiglio Nazionale delle Ricerche (CNR), VIII Strada 5, I-95121, Catania, Italy. ³Dipartimento di Fisica, Università di Roma "Tor Vergata", Via della Ricerca Scientifica 1, I-00133, Rome, Italy. Correspondence and requests for materials should be addressed to E.Z. (email: zallo@pdi-berlin.de)

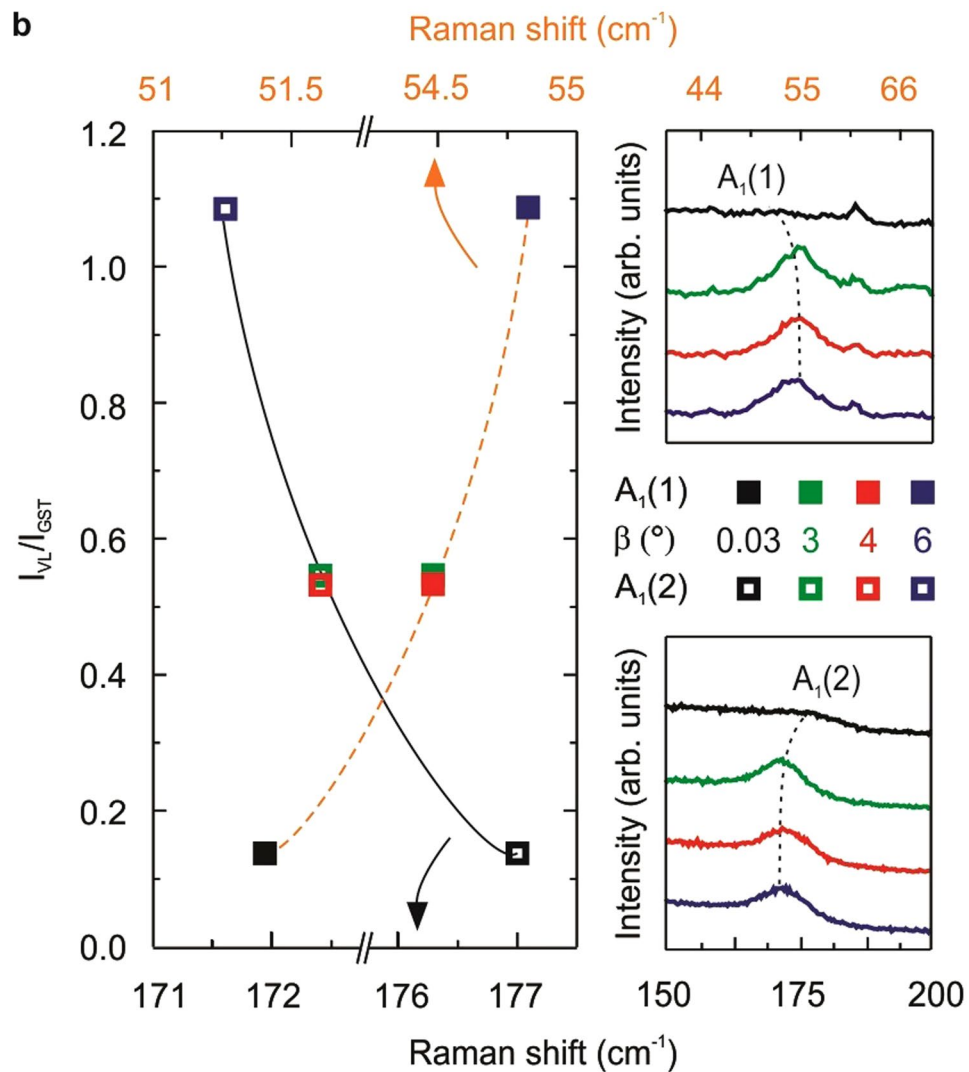


Figure 1. Stable rhombohedral stacking with almost pure GST124 on substrate miscut. (a) Raman spectra of 70 nm-thick GST grown on Si (111) with $\beta=0.03^\circ$ at RT (black), $\beta=4^\circ$ at RT (red) and $\beta=4^\circ$ at 10 K (dark red). (b) Intensity ratio of the second order XRD for the VL peak and GST peak ($I_{\text{VL}}/I_{\text{GST}}$) as a function of the Raman shift for the $A_1(1)$ (full squares) and $A_1(2)$ (empty squares) modes with $\beta=0.03^\circ$ (black), 3° (green), 4° (red) and 6° (blue). Dashed and solid lines serve as a guide to the eye. The top and bottom right panels show the Raman shift of the $A_1(1)$ and $A_1(2)$ modes, respectively. (c) 70 nm- (red) or 7 nm- (light blue) thick GST grown on Si (111) with $\beta=4^\circ$.



Open Access This article is licensed under a Creative Commons Attribution 4.0 International License, which permits use, sharing, adaptation, distribution and reproduction in any medium or format, as long as you give appropriate credit to the original author(s) and the source, provide a link to the Creative Commons license, and indicate if changes were made. The images or other third party material in this article are included in the article's Creative Commons license, unless indicated otherwise in a credit line to the material. If material is not included in the article's Creative Commons license and your intended use is not permitted by statutory regulation or exceeds the permitted use, you will need to obtain permission directly from the copyright holder. To view a copy of this license, visit <http://creativecommons.org/licenses/by/4.0/>.

© The Author(s) 2018